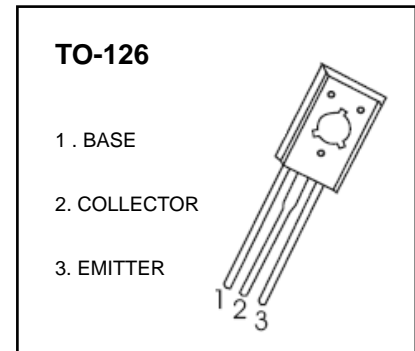


TO-126 Plastic-Encapsulate Transistor

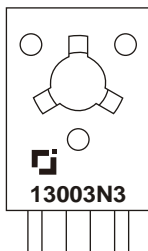
3DD13003N3 TRANSISTOR (NPN)

FEATURES

- Power switching applications
- Good high temperature
- Low saturation voltage
- High speed switching

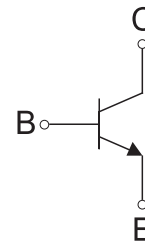


MARKING



Logo
13003N3=Device code

Equivalent Circuit



ORDERING INFORMATION

Part Number	Package	Packing Method	Pack Quantity
3DD13003N3	TO-126	Bulk	200pcs/Bag
3DD13003N3-TU	TO-126	Tube	60pcs/Tube

MAXIMUM RATINGS (T_a=25°C unless otherwise noted)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	700	V
V _{CEO}	Collector-Emitter Voltage	400	V
V _{EBO}	Emitter-Base Voltage	9	V
I _C	Collector Current	1.5	A
P _C	Collector Power Dissipation	1.25	W
R _{θJA}	Thermal Resistance From Junction To Ambient	100	°C/W
T _J , T _{stg}	Operation Junction and Storage Temperature Range	-55~+150	°C

ELECTRICAL CHARACTERISTICS

$T_a=25\text{ }^\circ\text{C}$ unless otherwise specified

Parameter	Symbol	Test conditions	Min	Typ	Max	Unit
Collector-base breakdown voltage	$V_{(BR)CBO}$	$I_C=1\text{mA}, I_E=0$	700			V
Collector-emitter breakdown voltage	$V_{(BR)CEO}$	$I_C=10\text{mA}, I_B=0$	400			V
Emitter-base breakdown voltage	$V_{(BR)EBO}$	$I_E=1\text{mA}, I_C=0$	9			V
Collector cut-off current	I_{CBO}	$V_{CB}=700\text{V}, I_E=0$			10	μA
Collector cut-off current	I_{CEO}	$V_{CE}=400\text{V}, I_B=0$			50	μA
Emitter cut-off current	I_{EBO}	$V_{EB}=9\text{V}, I_C=0$			10	μA
DC current gain	$h_{FE(1)}$	$V_{CE}=5\text{V}, I_C=0.2\text{A}$	10		40	
	$h_{FE(2)}$	$V_{CE}=5\text{V}, I_C=1\text{mA}$	8			
	$h_{FE(3)}$	$V_{CE}=5\text{V}, I_C=1.5\text{A}$	5			
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C=1\text{A}, I_B=0.2\text{A}$			0.5	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C=1\text{A}, I_B=0.25\text{A}$			1.5	V
Storage time	t_s	$I_C=250\text{mA}$ (UI9600)	2		4	μs

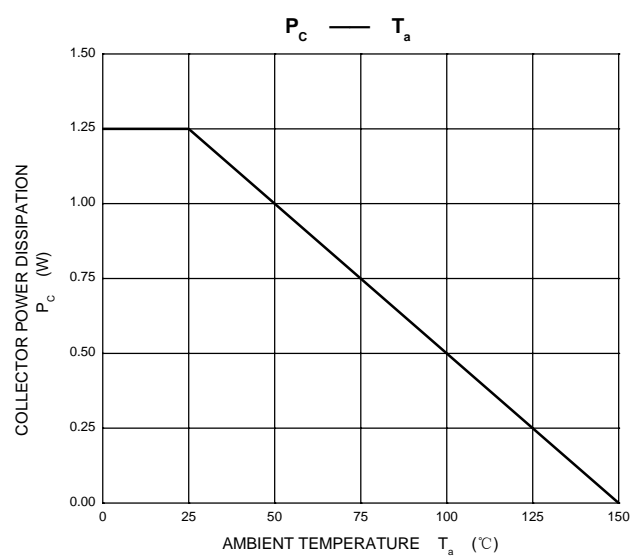
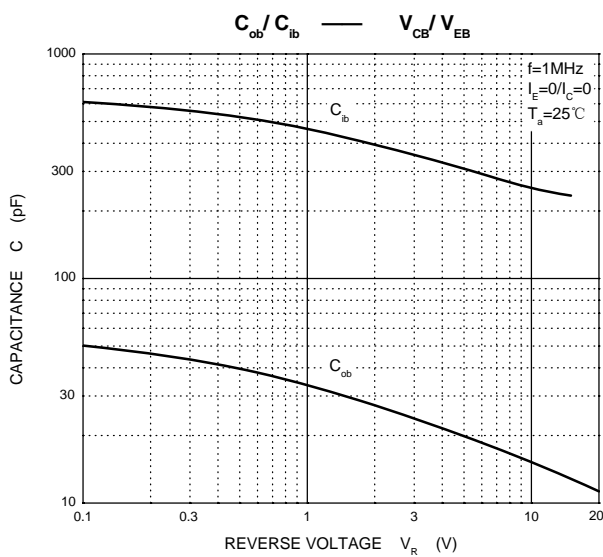
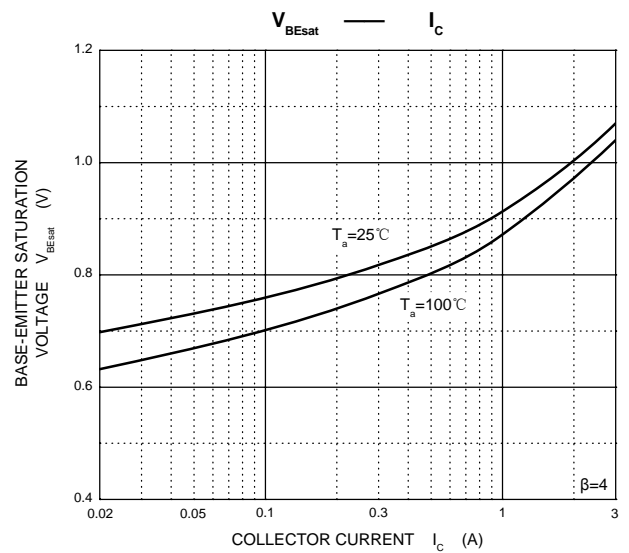
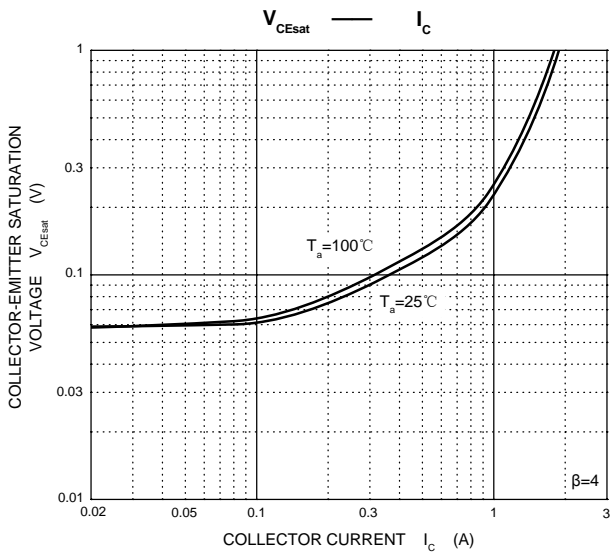
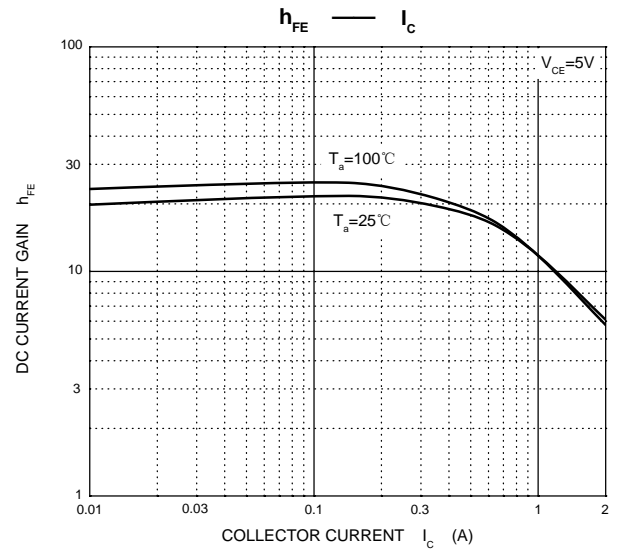
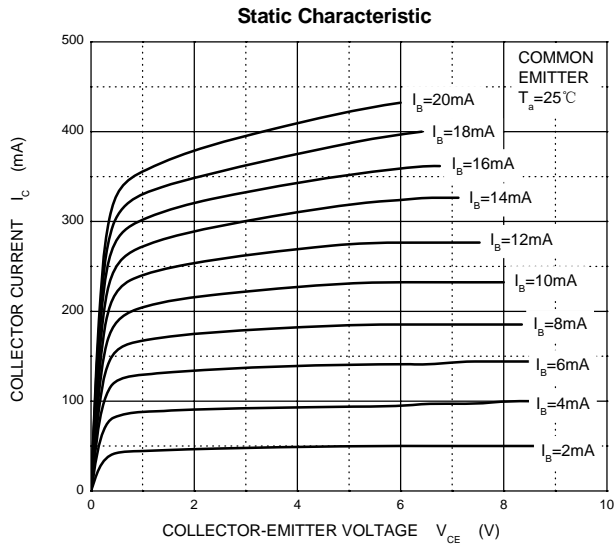
CLASSIFICATION OF $h_{FE(1)}$

Range	10-15	15-20	20-25	25-30	30-35	35-40

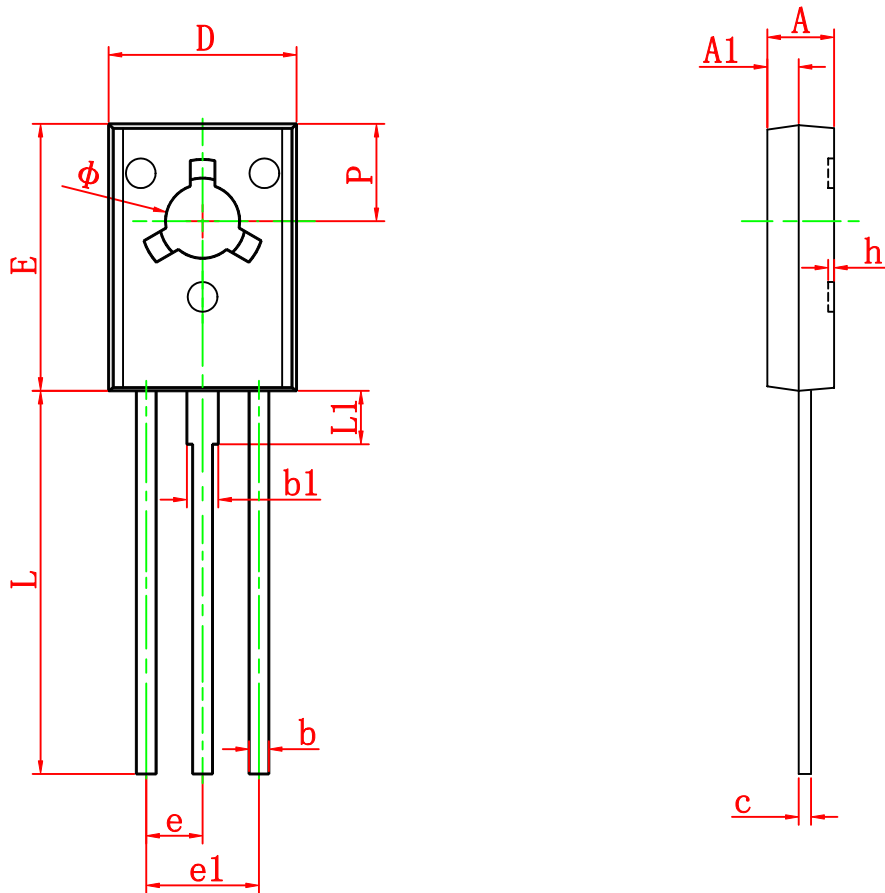
CLASSIFICATION OF t_s

Rank	A1	A2	B1	B2
Range	2-2.5 (μs)	2.5-3 (μs)	3-3.5 (μs)	3.5-4 (μs)

Typical Characteristics



TO-126 Package Outline Dimensions



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	2.500	2.900	0.098	0.114
A1	1.100	1.500	0.043	0.059
b	0.660	0.860	0.026	0.034
b1	1.170	1.370	0.046	0.054
c	0.450	0.600	0.018	0.024
D	7.400	7.800	0.291	0.307
E	10.600	11.000	0.417	0.433
e	2.290 TYP		0.090 TYP	
e1	4.480	4.680	0.176	0.184
h	0.000	0.300	0.000	0.012
L	15.300	15.700	0.602	0.618
L1	2.100	2.300	0.083	0.091
P	3.900	4.100	0.154	0.161
ϕ	3.000	3.200	0.118	0.126

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